

General Description

The CMH40N20P uses advanced planar stripe DMOS technology and design to provide excellent RDS(ON).

These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- $V_{DS} = 200V, I_D = 50A$
 $R_{DS(ON)} = 57m\Omega @ V_{GS} = 10V$
- Low on-resistance
- Fast Switching
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current	50	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current	40	A
I_{DM}	Pulsed Drain Current	200	A
EAS	Single Pulse Avalanche Energy	640	mJ
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	280	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.4	$^\circ C/W$

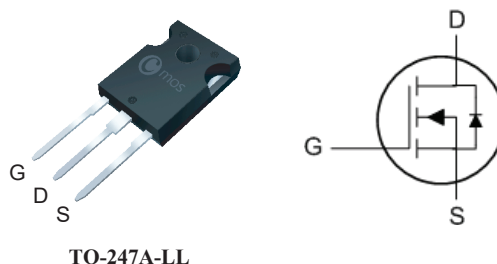
Product Summary

BVDSS	RDS(ON)	ID
200V	57m Ω	50A

Applications

- DC-AC converters
- SMPS Power
- UPS (Uninterruptible Power Supply)

TO-247A-LL Pin Configuration



TO-247A-LL

Type	Package	Marking
CMH40N20P	TO-247	CMH40N20P

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	200	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	---	57	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=200V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	25	---	S
Q_g	Total Gate Charge	$I_D=50A$	---	83	---	nC
Q_{gs}	Gate-Source Charge	$V_{DD}=160V$	---	25	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=10V$	---	43	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=100V$, $R_G=4.7\Omega$	---	34	---	ns
T_r	Rise Time	$I_D=25A$, $V_{GS}=10V$	---	64	---	
$T_{d(off)}$	Turn-Off Delay Time	$V_{DD}=160V$, $R_G=4.7\Omega$	---	17	---	
T_f	Fall Time	$I_D=50A$, $V_{GS}=10V$	---	26	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	3400	---	pF
C_{oss}	Output Capacitance		---	900	---	
C_{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	50	A
I_{SM}	Pulsed Source Current		---	---	200	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=30A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

This product has been designed and qualified for the consumer market.
 Cmos assumes no liability for customers' product design or applications.
 Cmos reserves the right to improve product design ,functions and reliability without notice.